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Vibrational study of the initial stages of the oxidation of Si(111) and Si(100) surfaces

DOI: 10.1007/bf00617767

Applied Physics A: Solids and Surfaces, 1982, 29, 113-124.

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336	Dissociation of water molecules on Si surfaces. <b>1983</b> , 27, 5180-5183		76
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334	Hydrogen and oxygen bonding on silicon surfaces. <b>1983</b> , 165-177		5
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